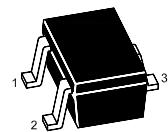


MMBTSC3356W

NPN Silicon Epitaxial Planar Transistor

for microwave low noise amplifier at VHF, UHF and CATV band.



The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.

1.Base 2.Emitter 3.Collector
SOT-323 Plastic Package

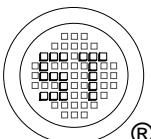
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	20	V
Collector Emitter Voltage	V_{CEO}	12	V
Emitter Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 65 to + 150	°C

Characteristics at $T_{amb} = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$ Current Gain Group	h_{FE}	50	-	100	-
	h_{FE}	80	-	160	-
	h_{FE}	125	-	250	-
Collector Cutoff Current at $V_{CB} = 10 \text{ V}$	I_{CBO}	-	-	1	μA
Emitter Cutoff Current at $V_{EB} = 1 \text{ V}$	I_{EBO}	-	-	1	μA
Collector Base Breakdown Voltage at $I_C = 10 \mu\text{A}$	$V_{(BR)CBO}$	20	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$	$V_{(BR)CEO}$	12	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \mu\text{A}$	$V_{(BR)EBO}$	3	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$, $I_B = 5 \text{ mA}$	$V_{CE(sat)}$	-	-	0.5	V
Gain Bandwidth Product at $V_{CE} = 10 \text{ V}$, $I_C = 20 \text{ mA}$	f_T	-	7	-	GHz
Feed-Back Capacitance at $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	$C_{re}^{1)}$	-	-	1	pF

¹⁾ The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.

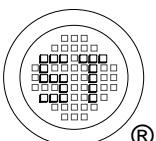
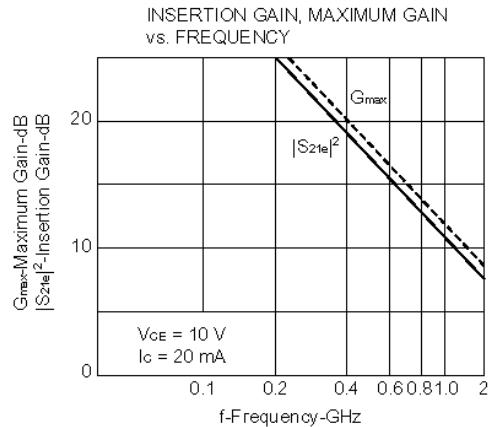
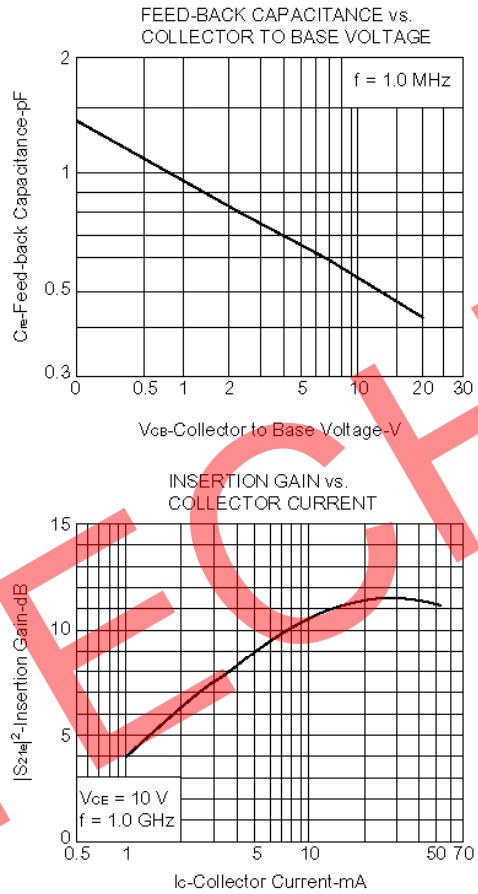
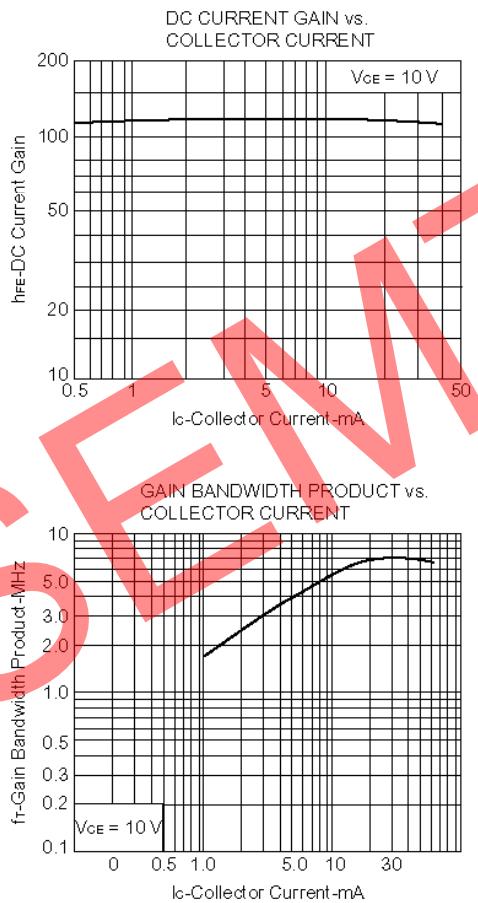
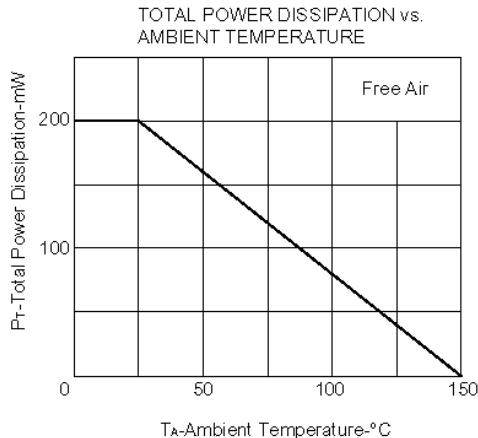


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MMBTSC3356W

TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



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